

Product Summary

BV_{DSS}	R_{DS(ON)} Max	I_D Max T_A = 25°C
-30V	17mΩ @ V _{GS} = -10V	-8.6A
	25mΩ @ V _{GS} = -4.5V	-7.1A

Features and Benefits

- Low R_{DS(ON)} – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

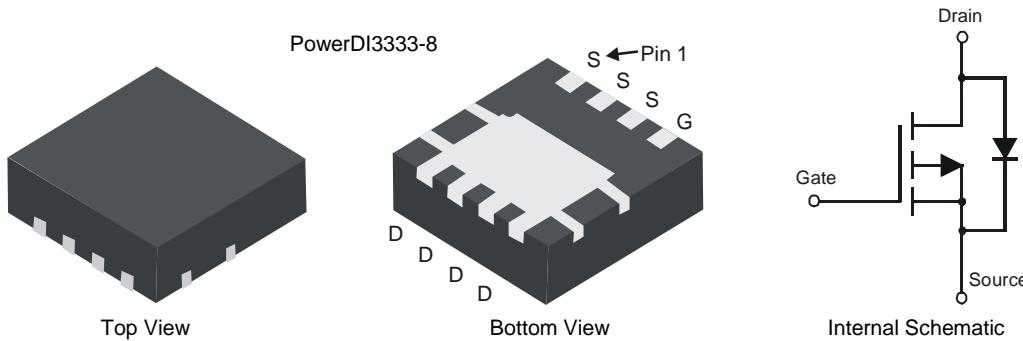
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.008 grams (Approximate)



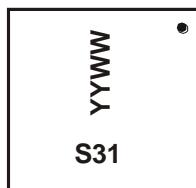
Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3008SFGQ-7	PowerDI3333-8	2,000/Tape & Reel
DMP3008SFGQ-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



S31 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last digit of year (ex: 11 = 2011)
 WW = Week code (01 ~ 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 7) $V_{GS} = -10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-8.6 -7.0	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-11.7 -9.3	A
Continuous Drain Current (Note 7) $V_{GS} = -4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-7.1 -5.6	A
	$t < 10\text{s}$	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-9.6 -7.6	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	-80	A
Maximum Continuous Body Diode Forward Current (Note 7)			I_S	-3.0	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		P_D	0.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	140	$^\circ\text{C/W}$
	$t < 10\text{s}$		72	$^\circ\text{C/W}$
Total Power Dissipation (Note 7)		P_D	2.2	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	57	$^\circ\text{C/W}$
	$t < 10\text{s}$		30	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	7.1	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

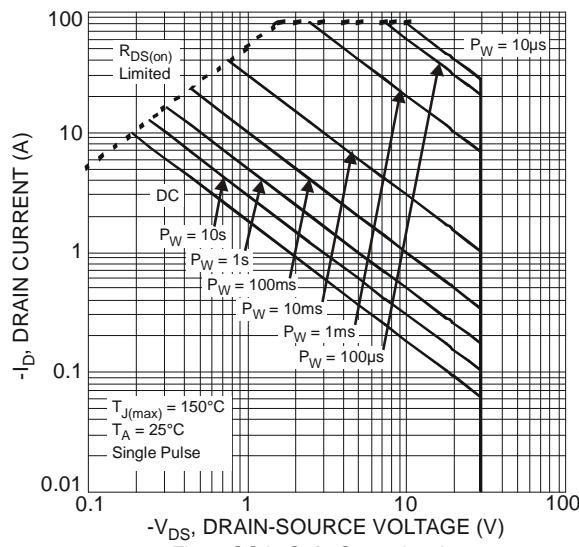


Fig. 1 SOA, Safe Operation Area

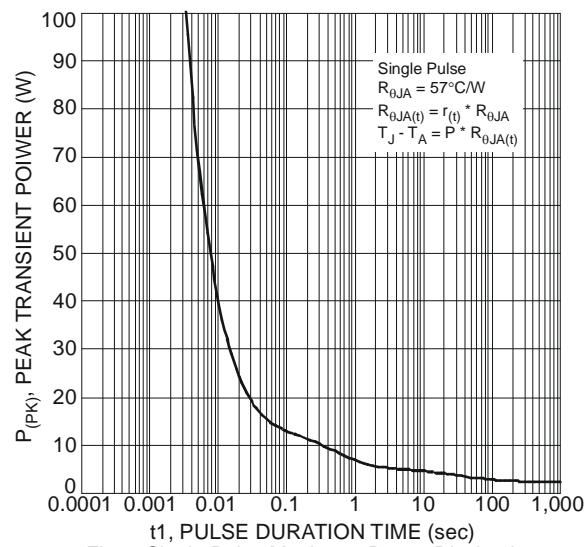


Fig. 2 Single Pulse Maximum Power Dissipation

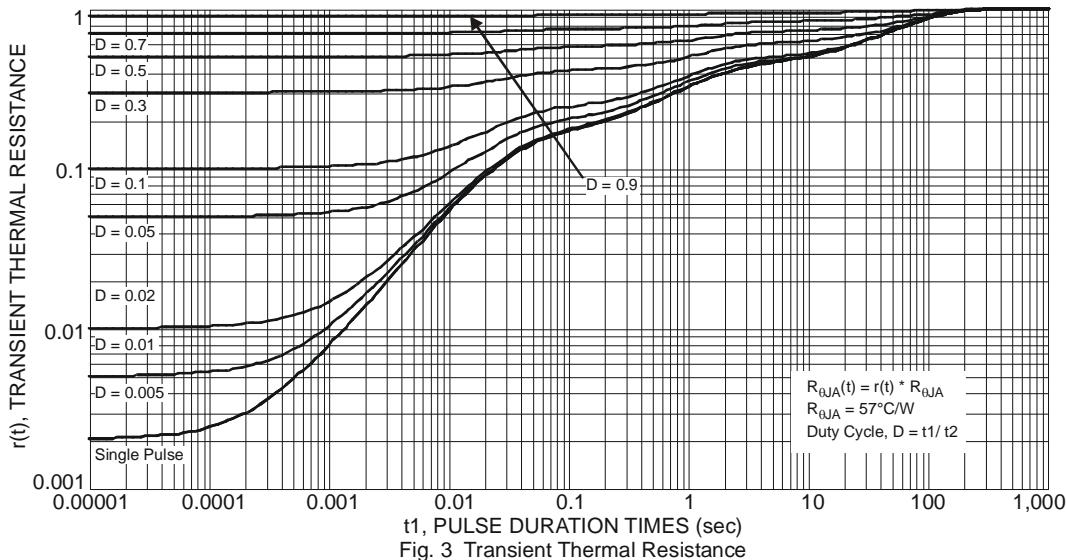


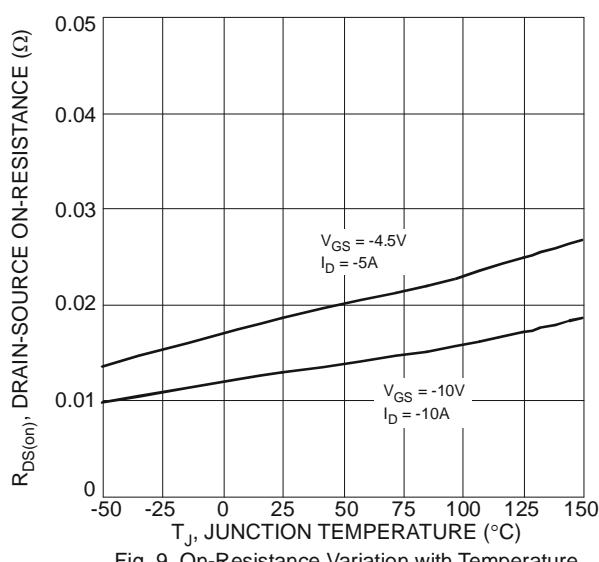
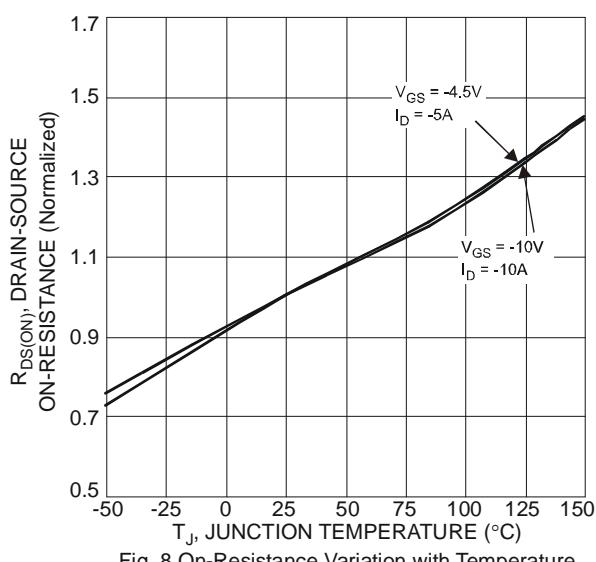
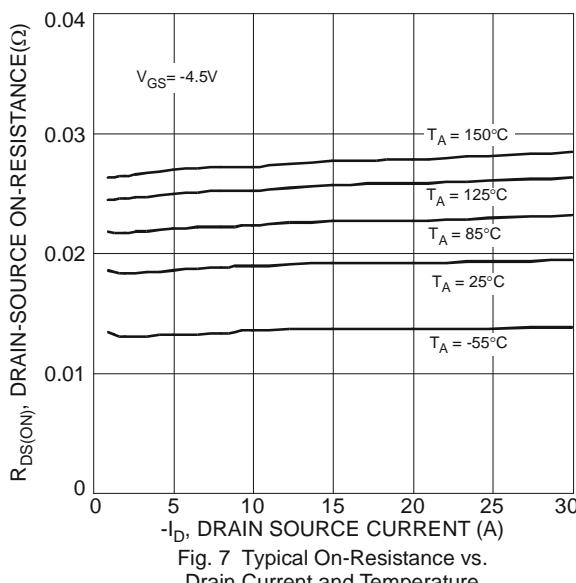
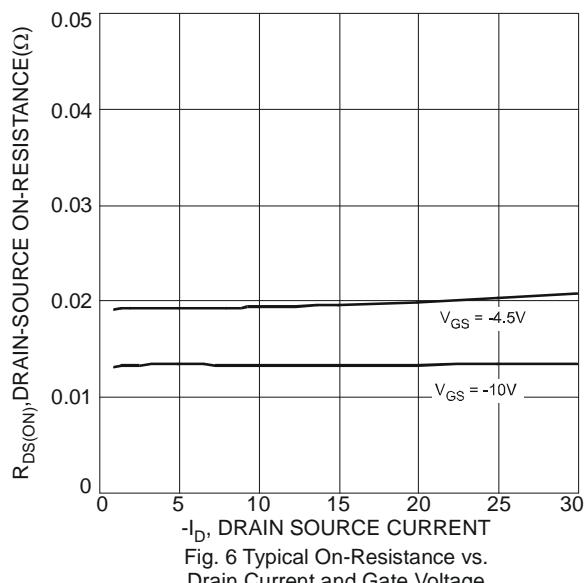
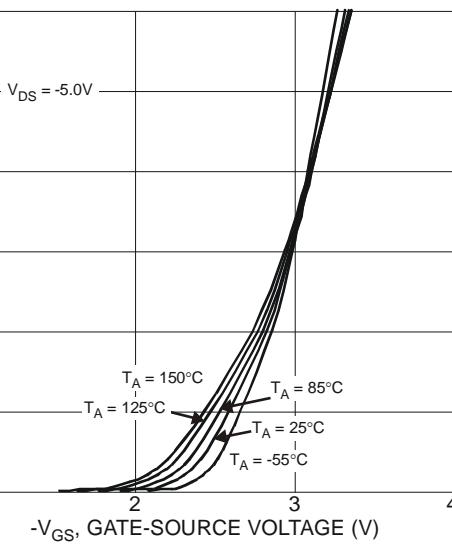
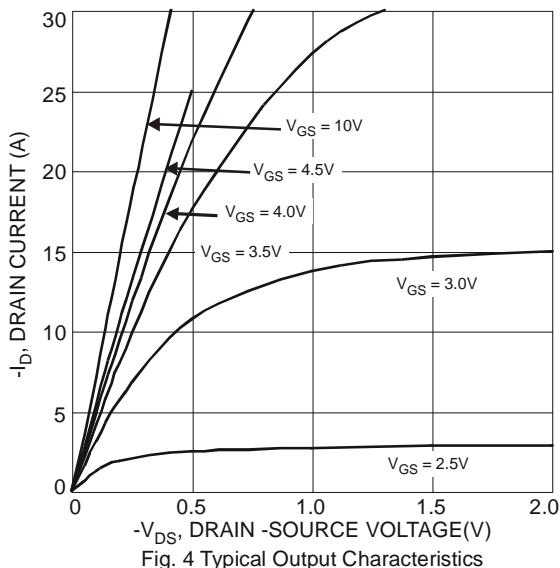
Fig. 3 Transient Thermal Resistance

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	$\text{V}_{\text{GS}} = 0\text{V}$, $\text{I}_D = -250\mu\text{A}$	
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1.0	μA	$\text{V}_{\text{DS}} = -30\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$	
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$\text{V}_{\text{GS}} = \pm 20\text{V}$, $\text{V}_{\text{DS}} = 0\text{V}$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$\text{V}_{\text{GS(th)}}$	-1.1	-1.6	-2.1	V	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}$, $\text{I}_D = -250\mu\text{A}$	
Static Drain-Source On-Resistance	$\text{R}_{\text{DS(ON)}}$	—	12.5	17	$\text{m}\Omega$	$\text{V}_{\text{GS}} = -10\text{V}$, $\text{I}_D = -10\text{A}$	
		—	18.5	25		$\text{V}_{\text{GS}} = -4.5\text{V}$, $\text{I}_D = -10\text{A}$	
Forward Transfer Admittance	$ \text{Y}_{\text{fs}} $	—	13	—	S	$\text{V}_{\text{DS}} = -15\text{V}$, $\text{I}_D = -10\text{A}$	
Diode Forward Voltage	V_{SD}	—	-0.7	-1.0	V	$\text{V}_{\text{GS}} = 0\text{V}$, $\text{I}_s = -1\text{A}$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C_{iss}	—	2,230	—	pF	$\text{V}_{\text{DS}} = -15\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$ $f = 1.0\text{MHz}$	
Output Capacitance	C_{oss}	—	328	—			
Reverse Transfer Capacitance	C_{rss}	—	294	—			
Gate Resistance	R_{G}	—	6.4	—	Ω	$\text{V}_{\text{DS}} = 0\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$, $f = 1.0\text{MHz}$	
Total Gate Charge ($\text{V}_{\text{GS}} = -10\text{V}$)	Q_{g}	—	47	—	nC	$\text{V}_{\text{DS}} = -15\text{V}$, $\text{I}_D = -10\text{A}$	
Total Gate Charge ($\text{V}_{\text{GS}} = -4.5\text{V}$)	Q_{g}	—	23	—			
Gate-Source Charge	Q_{gs}	—	9.4	—			
Gate-Drain Charge	Q_{gd}	—	5.6	—			
Turn-On Delay Time	$\text{t}_{\text{D(ON)}}$	—	10.5	—	nS	$\text{V}_{\text{GS}} = -10\text{V}$, $\text{V}_{\text{DS}} = -15\text{V}$, $\text{R}_{\text{G}} = 6\Omega$	
Turn-On Rise Time	t_{R}	—	8.5	—			
Turn-Off Delay Time	$\text{t}_{\text{D(OFF)}}$	—	90	—			
Turn-Off Fall Time	t_{F}	—	40	—			

Notes: 8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



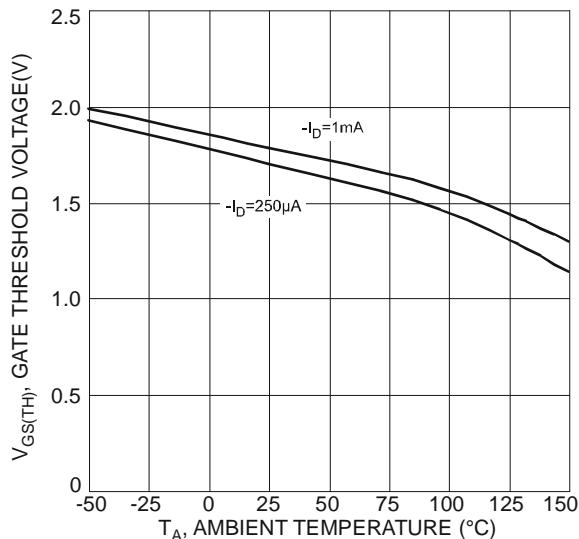


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

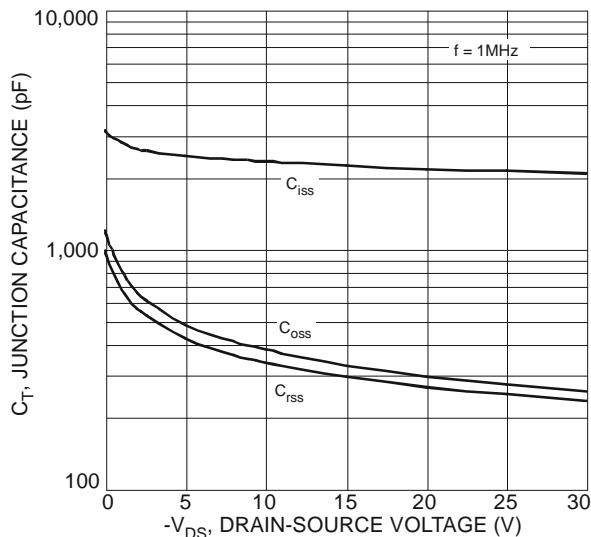


Fig. 12 Typical Junction Capacitance

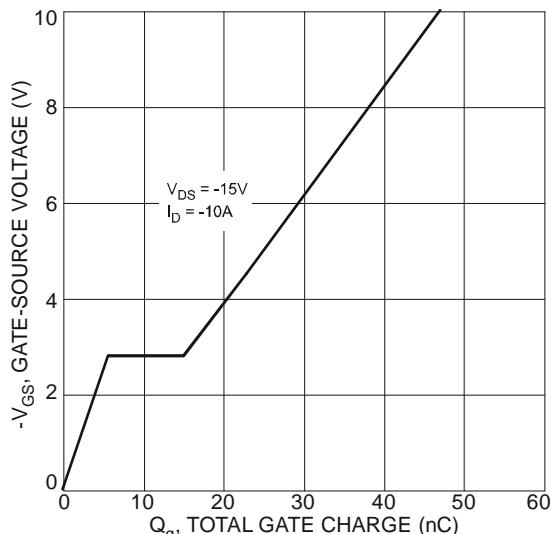


Fig. 14 Gate-Charge Characteristics

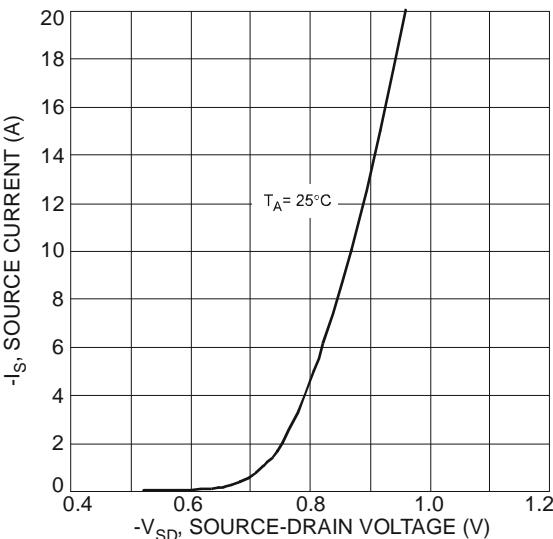


Fig. 11 Diode Forward Voltage vs. Current

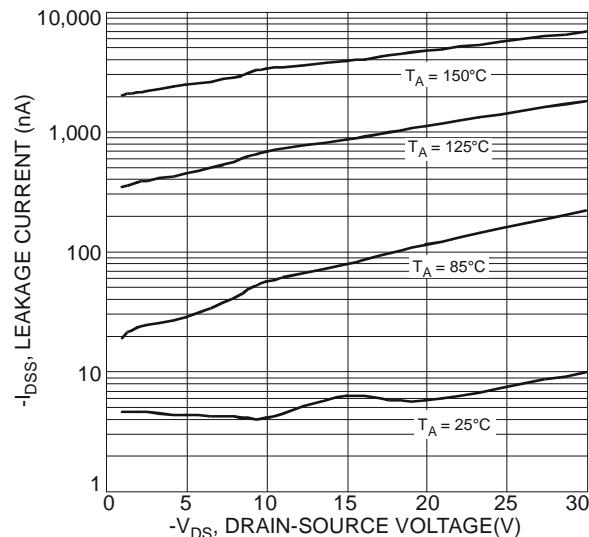
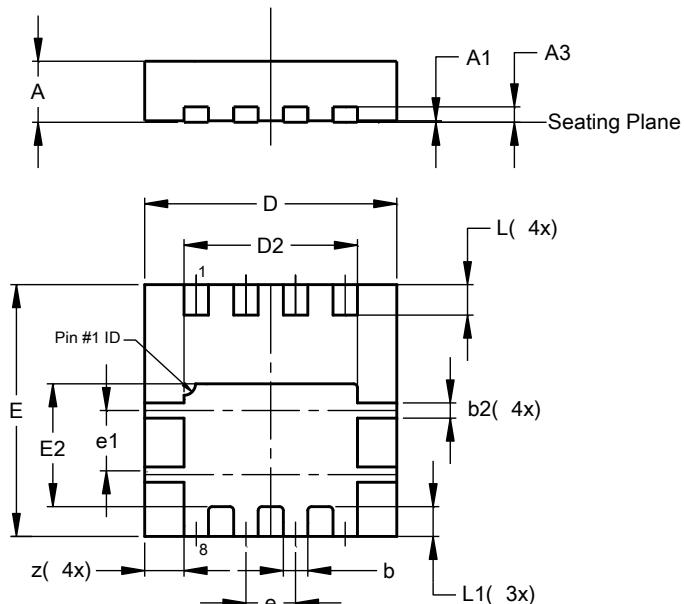


Fig. 13 Typical Drain-Source Leakage Current vs. Voltage

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

PowerDI3333-8



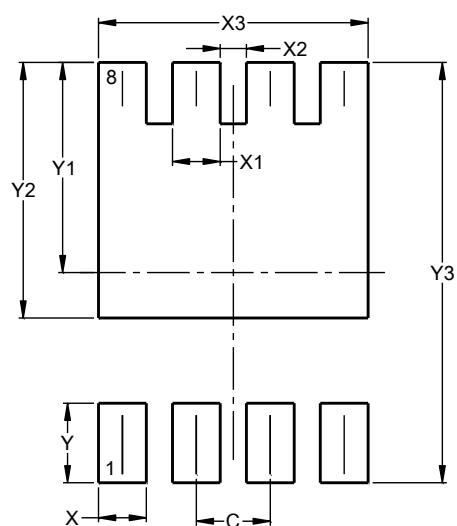
PowerDI3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	—	—	0.203
b	0.27	0.37	0.32
b2	—	—	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	—	—	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	—	—	0.39
z	—	—	0.515

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700

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